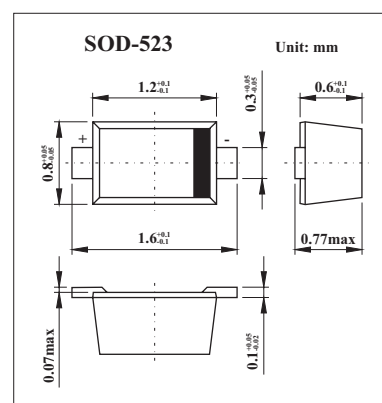


Silicon Schottky Barrier Diode

HSC276

■ Features

- High forward current, Low capacitance.
- Ultra small Flat Package (UFP) is suitable for surface mount design.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	3	V
Average rectified current	I_o	30	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse voltage	V_R	$I_R = 10\ \mu\text{A}$	30			V
Reverse current	I_R	$V_R = 0.5\text{ V}$			0.5	μA
Forward voltage	I_F	$V_R = 0.5\text{ V}$	35			mA
Capacitance	C	$V_R = 0.5\text{ V}, f = 1\text{ MHz}$			0.85	pF
ESD-Capability (Note 1)		C=200pF, Both forward and reverse direction 1 pulse.	30			V

Note

1. Failure criterion ; $I_R \geq 100\text{mA}$ at $V_R = 0.5\text{ V}$

■ Marking

Marking	C2
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